



SANYO Semiconductors

## DATA SHEET

# 2SB926 / 2SD1246

PNP / NPN Epitaxial Planar Silicon Transistors  
Large-Current Driving Applications

## Applications

- Power supplies, relay drivers, lamp drivers, electrical equipment.

## Features

- Adoption of FBET, MBIT processes.
- Low saturation voltage.
- Large current capacity and wide ASO.

## Specifications ( ) : 2SB926

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CB0</sub>		(-)30	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(-)25	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	I <sub>C</sub>		(-)2	A
Collector Current (Pulse)	I <sub>CP</sub>		(-)5	A
Collector Dissipation	P <sub>C</sub>		0.75	W
Junction Temperature	T <sub>J</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

## Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)20V, I <sub>E</sub> =0A			(-)0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0A			(-)0.1	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)100mA	100*		560*	
	h <sub>FE2</sub>	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1.5A, pulse	65	130		
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA		150		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		(32)19		pF

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\* : The 2SB926 / 2SD1246 are classified by 100mA h<sub>FE</sub> as follows :

Rank	R	S	T	U
h <sub>FE</sub>	100 to 200	140 to 280	200 to 400	280 to 560

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# 2SB926 / 2SD1246

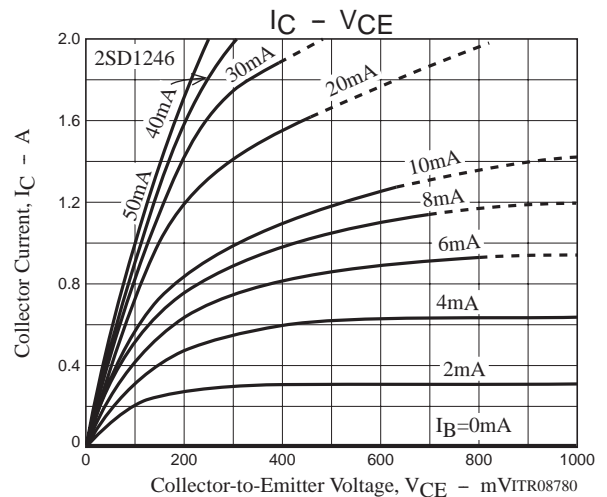
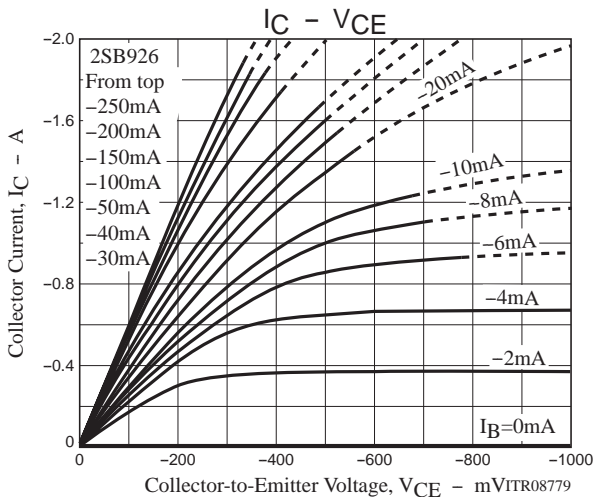
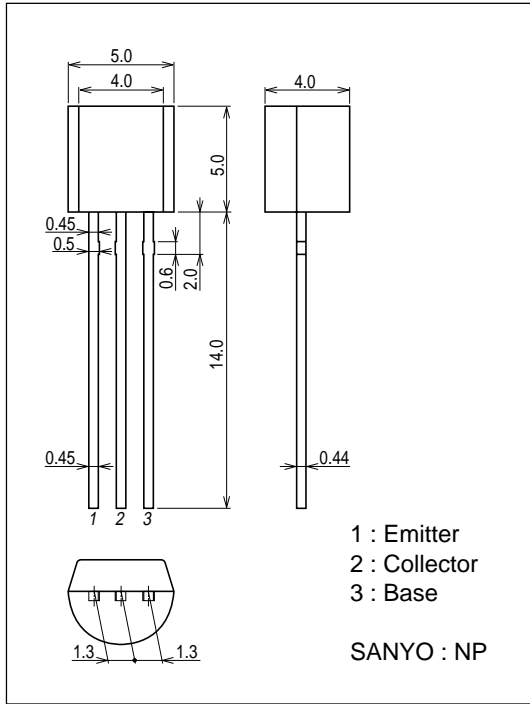
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA, \text{pulse}$		(-0.35)0.18	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		(-0.85)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-)30			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)25			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-)6			V

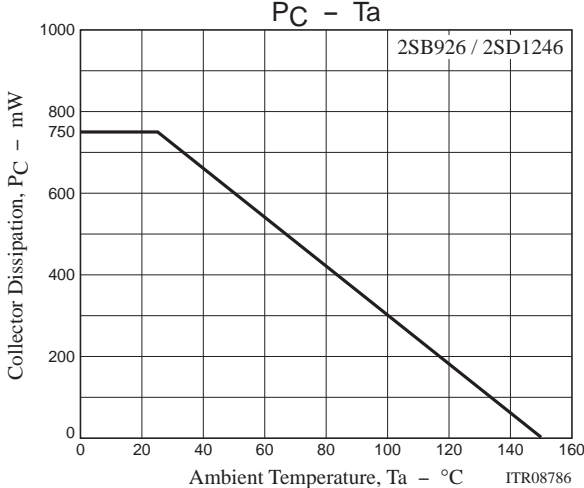
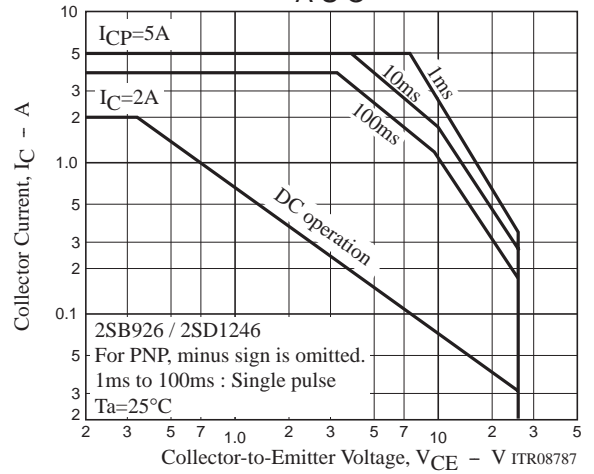
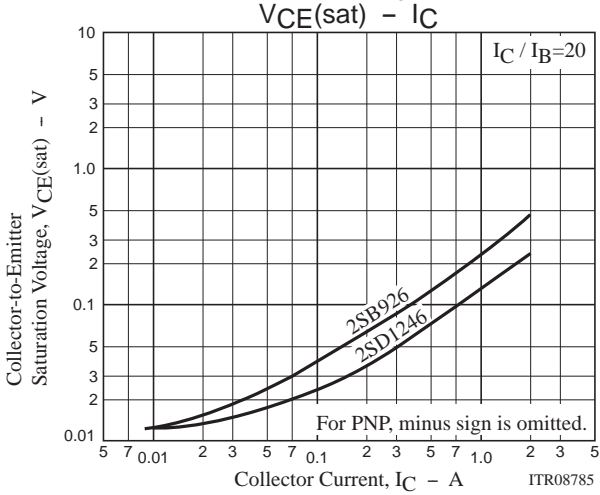
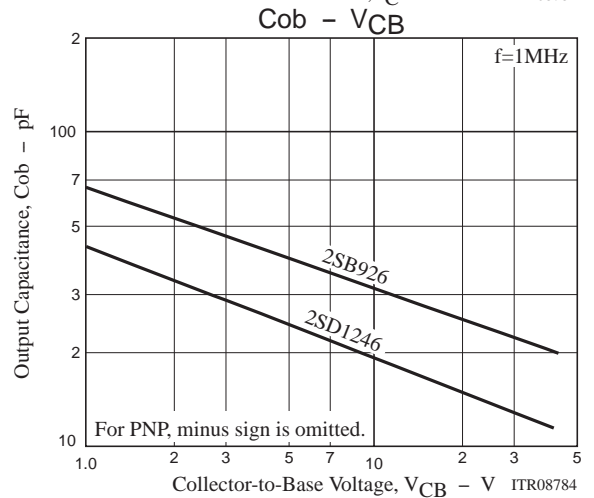
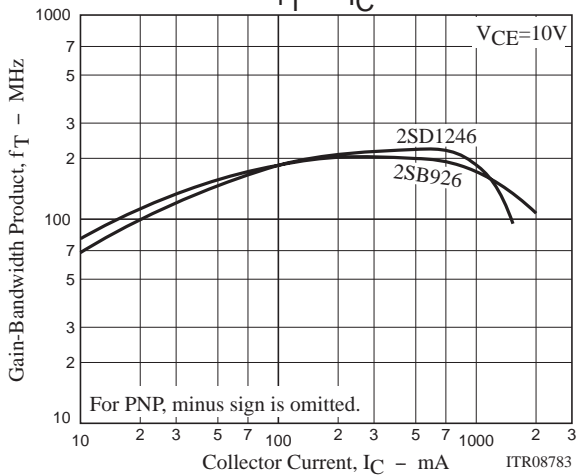
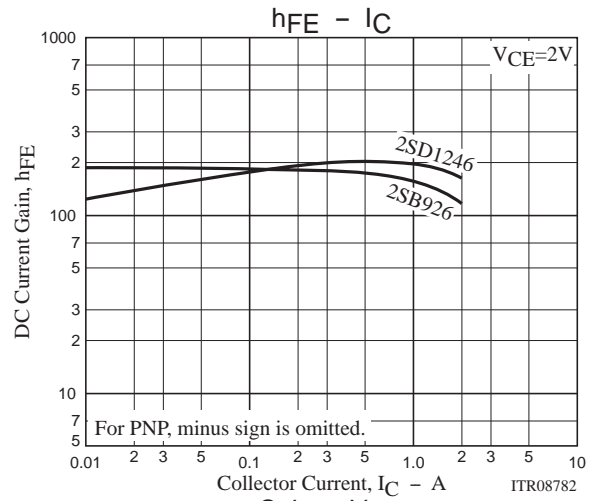
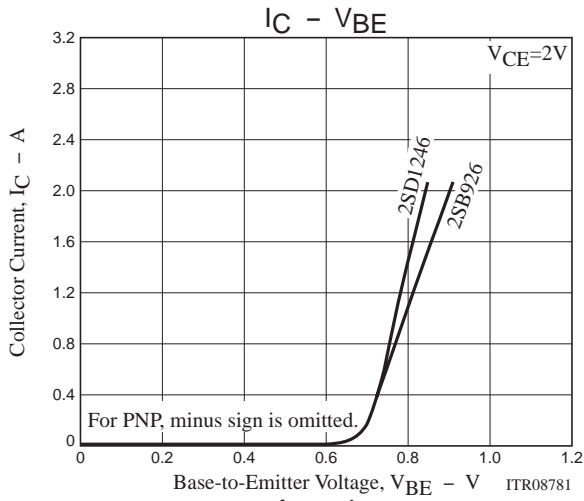
## Package Dimensions

unit : mm (typ)

7522-002



# 2SB926 / 2SD1246



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